

Supplementary Material

Eu³⁺ doped β -Ga₂O₃ Nanophosphors: Annealing Effect, Electronic Structure and Optical Spectroscopy

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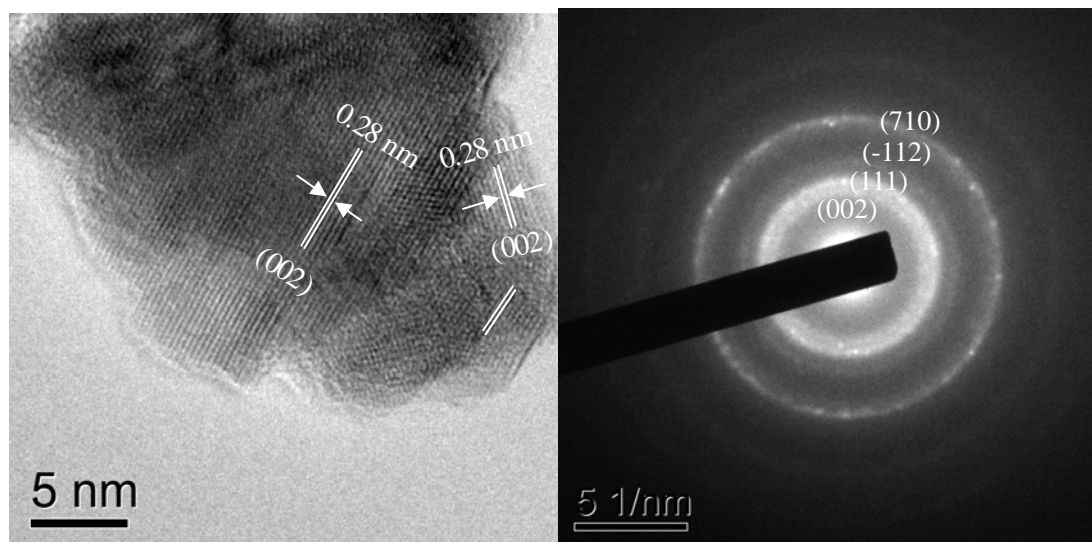


Figure S1 TEM and SAED images of the sample annealed at 650 °C.

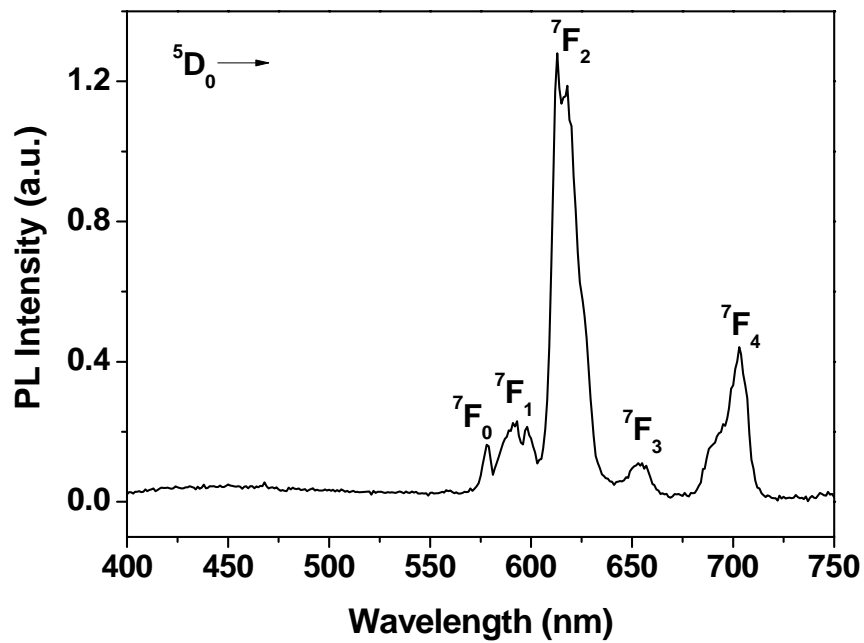


Figure S2 RT emission spectrum of 0.1 at.% Eu³⁺ doped β -Ga₂O₃ NCs annealed at 650 °C upon excitation at 285 nm.

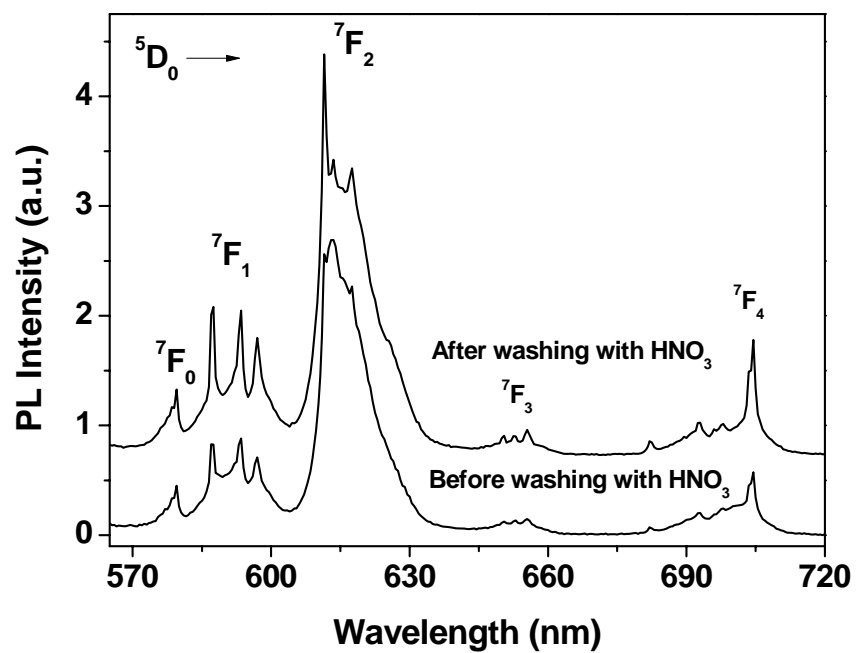


Figure S3 RT emission spectra of the sample annealed at 1000 °C before and after washing with diluted HNO₃ upon excitation at 285 nm.